

# Device Modeling Report

COMPONENTS : VOLTAGE COMPARATOR (CMOS)  
PART NUMBER : TC75W59FU  
MANUFACTURER : TOSHIBA



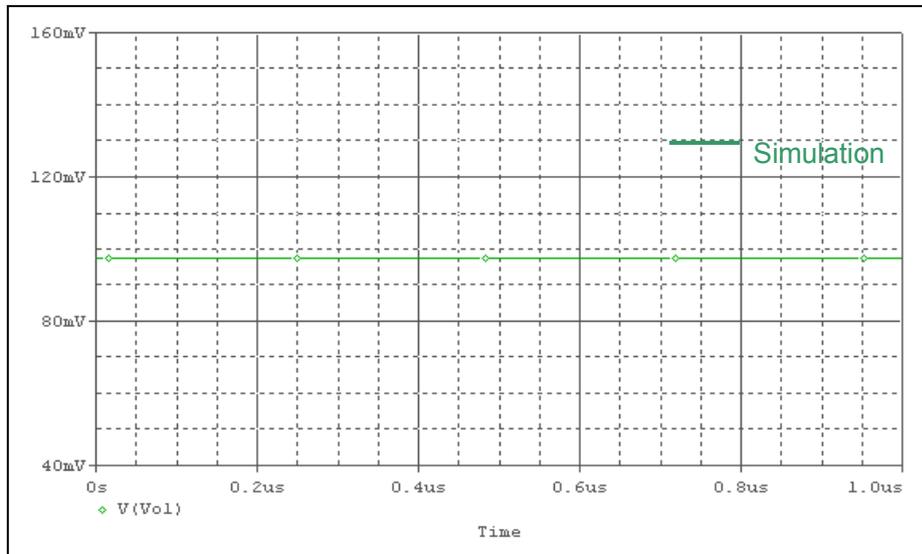
**Bee Technologies Inc.**

## MODEL PARAMETER

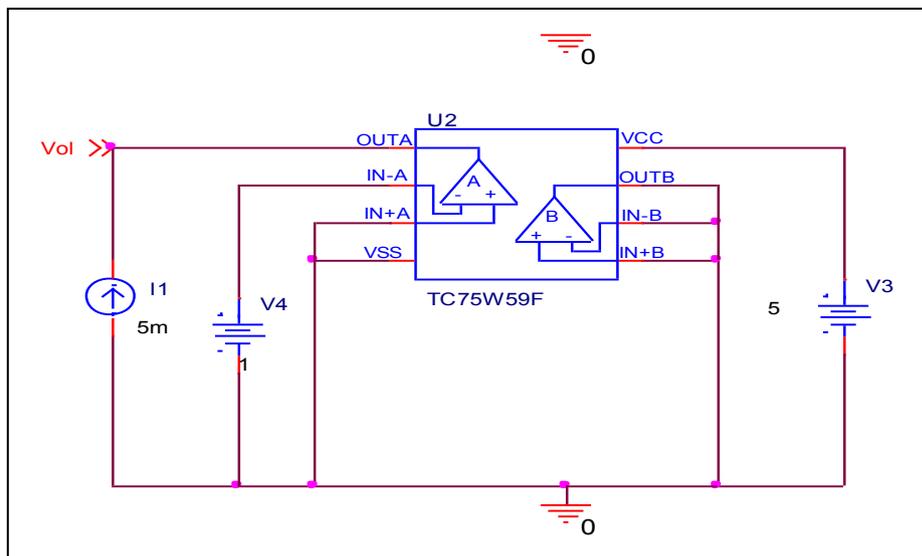
Pspice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Modility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

## Output Low Voltage

### Simulation result



### Evaluation Circuit

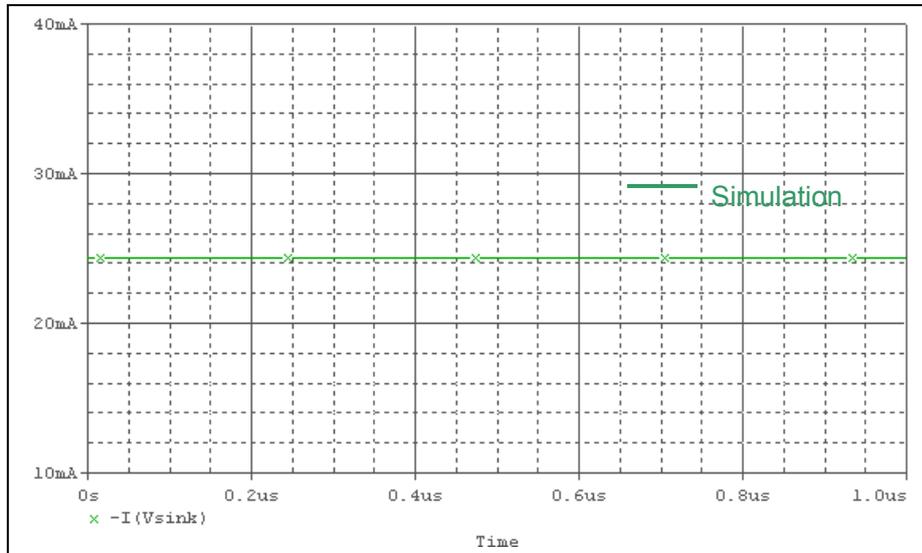


### Comparison Table

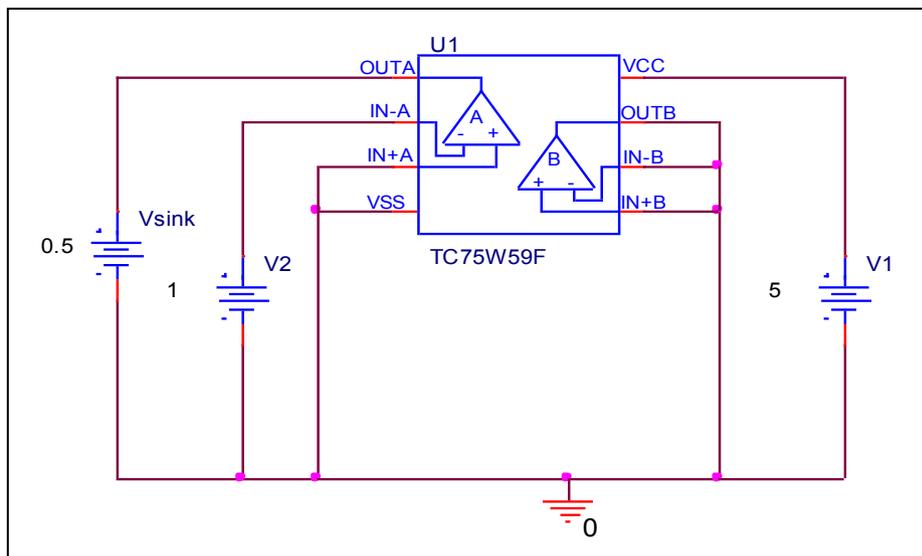
$I_{\text{sink}}=5\text{mA}$	Measurement	Simulation	%Error
$V_{\text{ol}} \text{ (V)}$	0.1	0.097472	-2.528

## Output Sink Current

### Simulation result



### Evaluation Circuit

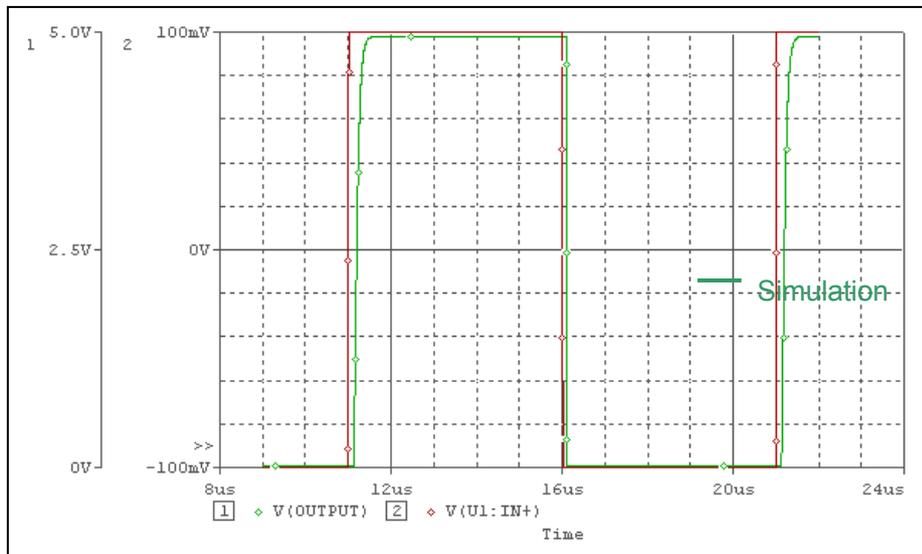


### Comparison Table

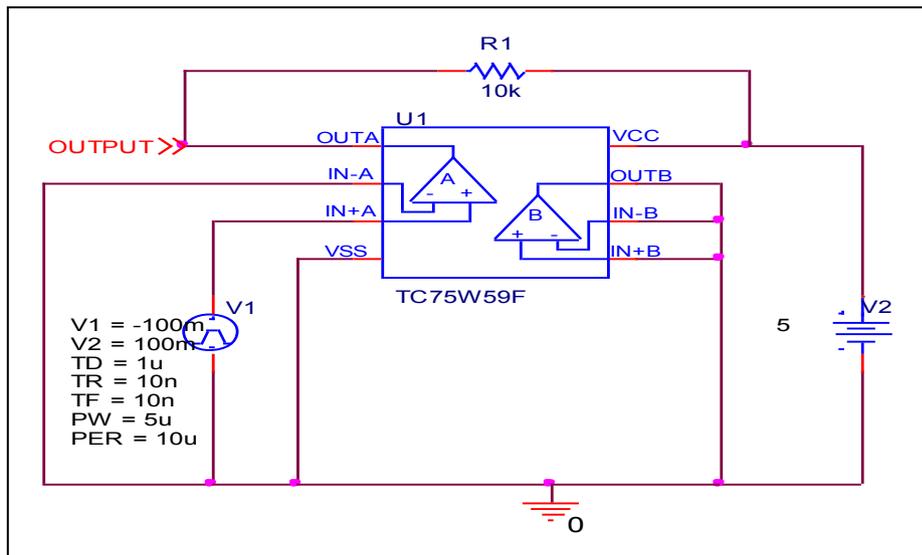
$V_{OL} = 0.5 \text{ V}$	Measurement	Simulation	%Error
$I_{\text{sink}} \text{ (mA)}$	25	24.375	-2.50

# Propagation Delay Time and Response Time

## Simulation result



## Evaluation Circuit

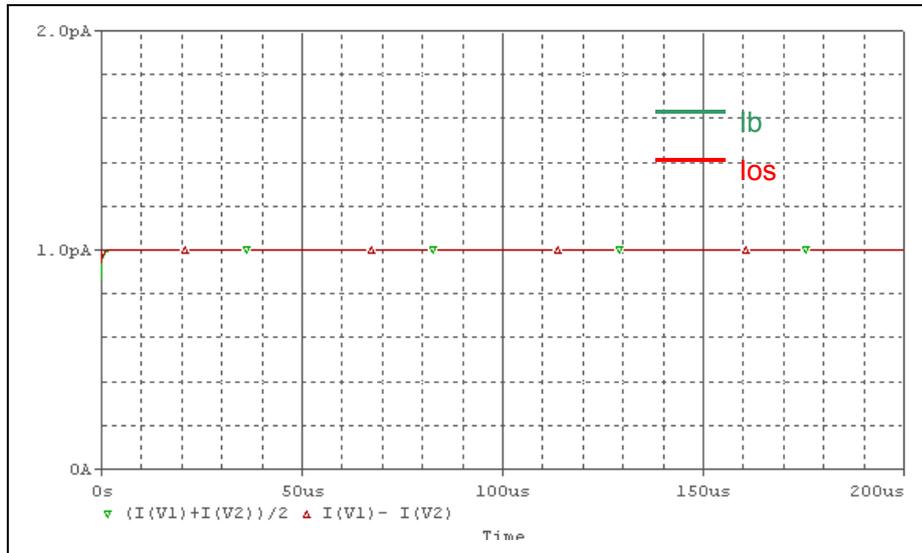


## Comparison Table

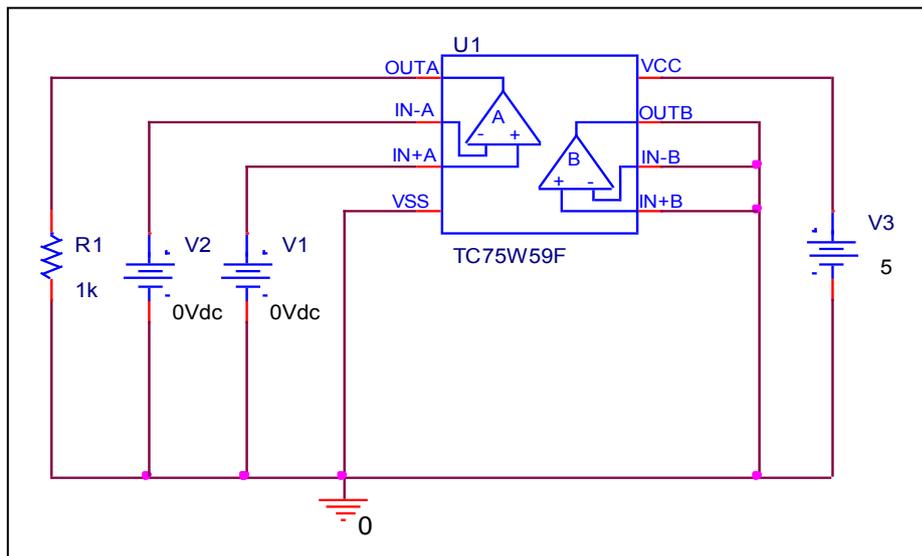
Over drive=100mV	Measurement	Simulation	%Error
$t_{PLH}$ (ns)	200	193.856	-3.072
$t_{PHL}$ (ns)	80	81.214	1.518
$t_r$ (ns)	160	159.177	-0.514
$t_f$ (ns)	3	2.9152	-2.827

# Input Bias Current and Input Offset Current Characteristics

## Simulation result



## Evaluation Circuit

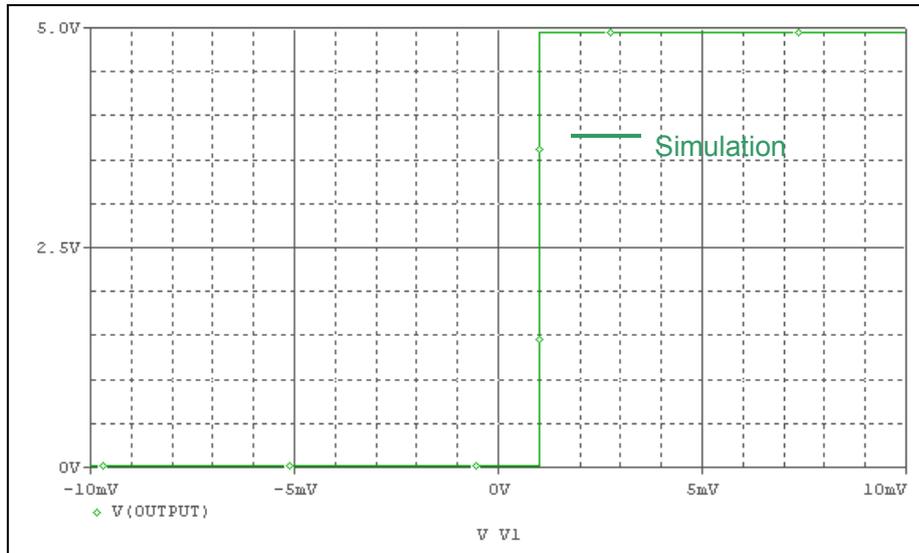


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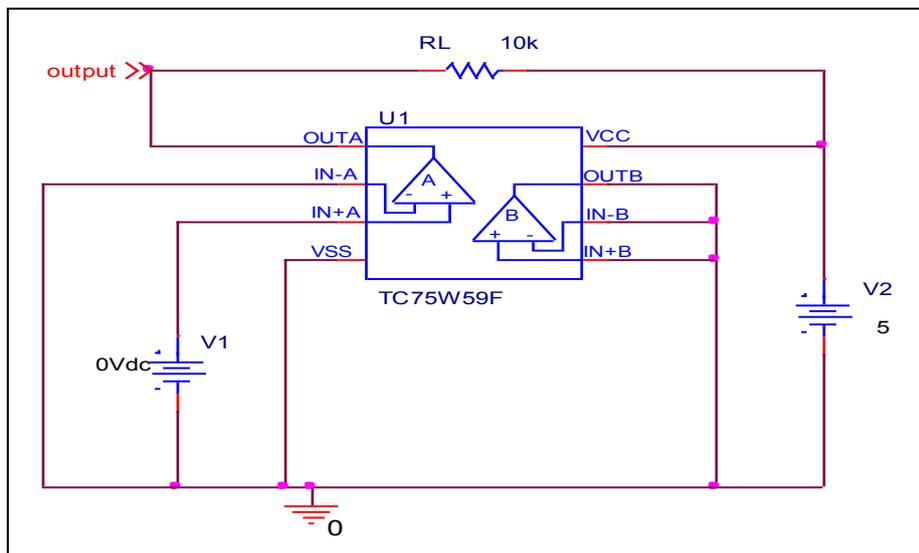
	Measurement	Simulation	%Error
$I_b$ (pA)	1	1	0
$I_{os}$ (pA)	1	1	0

# Input Offset Voltage Characteristics

## Simulation result



## Evaluation Circuit

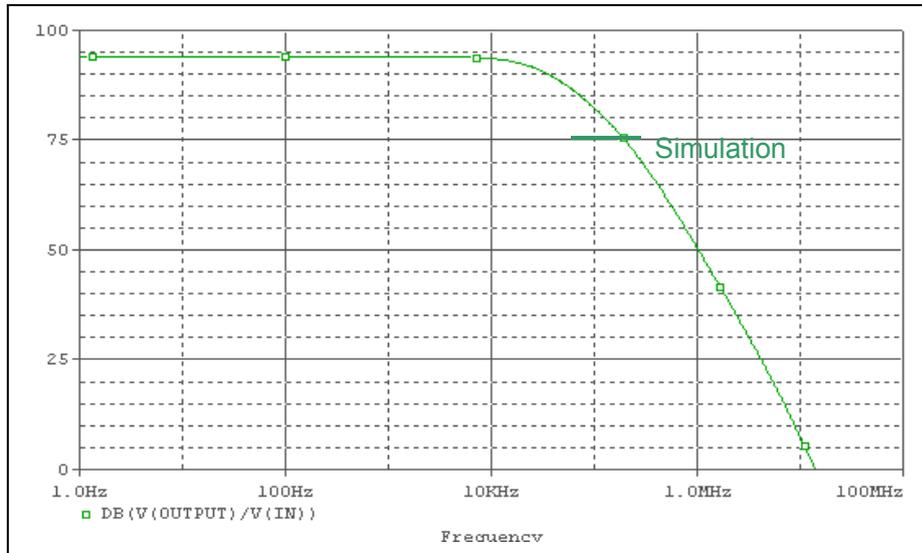


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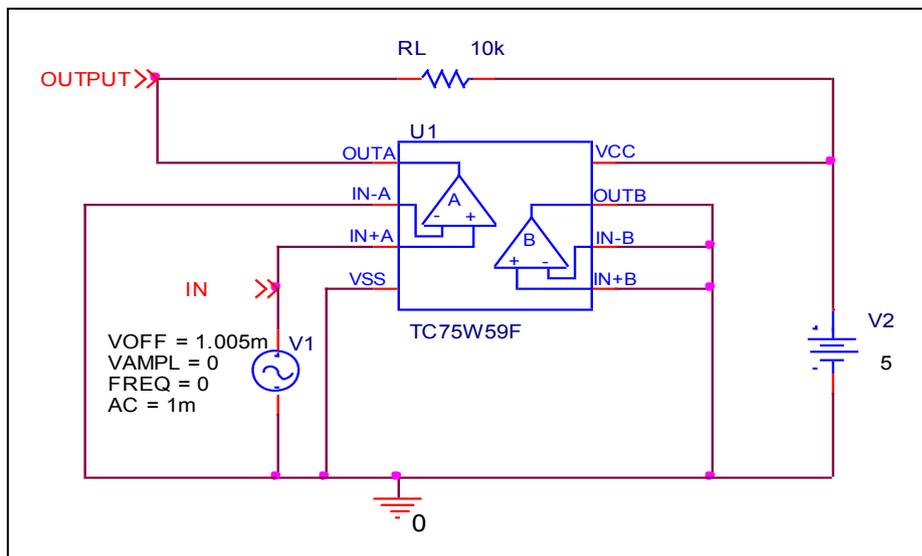
	Measurement	Simulation	%Error
$V_{io}(mV)$	1	1.005	0.5

# Voltage Gain Characteristics

## Simulation result



## Evaluation Circuit



## Comparison Table

	Measurement	Simulation	%Error
Av (dB)	94	93.995	-0.005